Electronic supplementary information

Formation of in-situ HVPE a-plane GaN nanodot: Effects on the structural properties of a-plane GaN template

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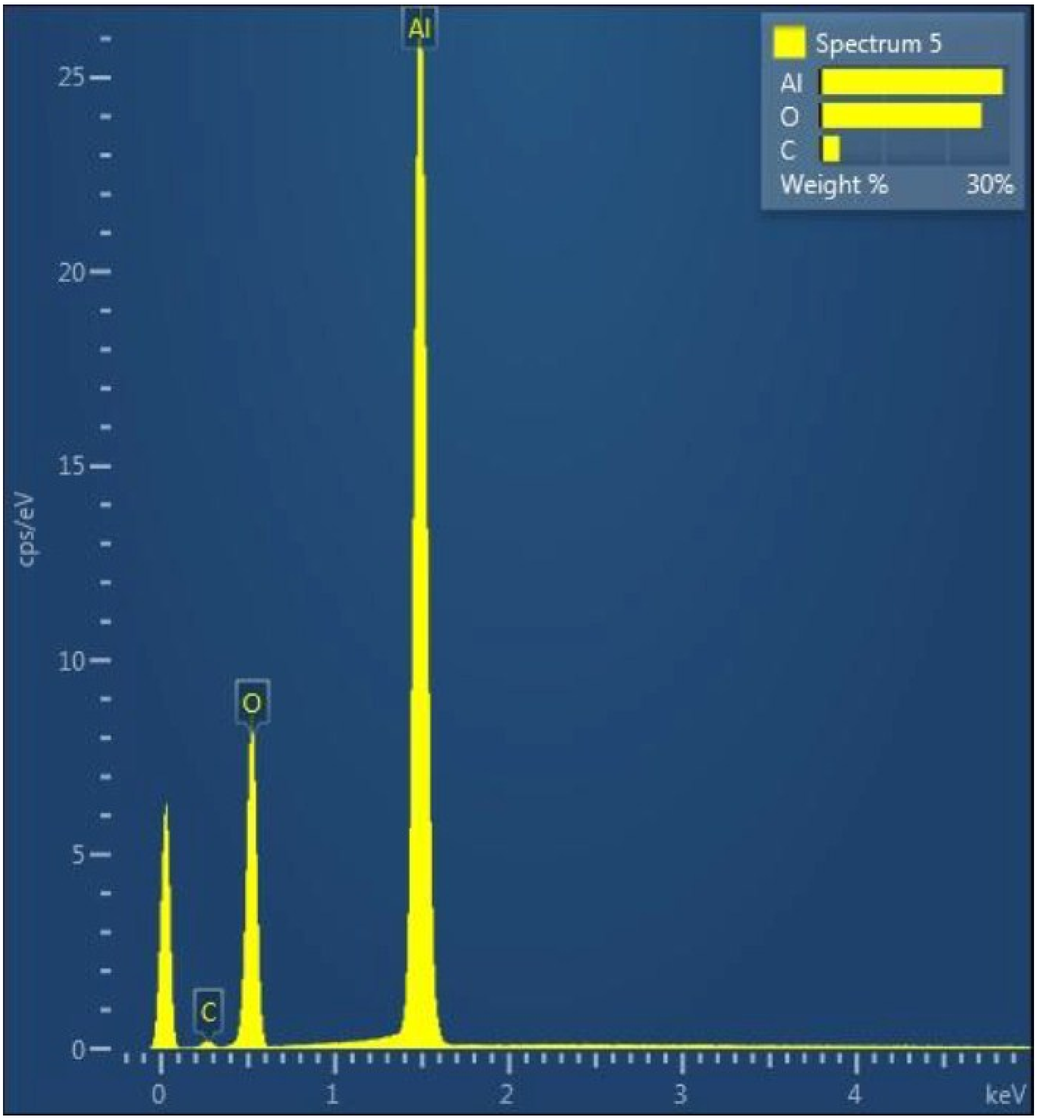

Element	Line Type	Apparent Concentration	Wt%	Atomic %
C	K series	0.36	3.11	8.86
O	K series	26.53	25.52	54.57
Al	K series	28.86	28.83	36.56
Total:			57.47	100.00

Fig. S1 EDX analysis of bare sapphire substrate without any surface treatment. Reproduced from Ref. 19 with permission from the Royal Society of Chemistry.